- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

Green

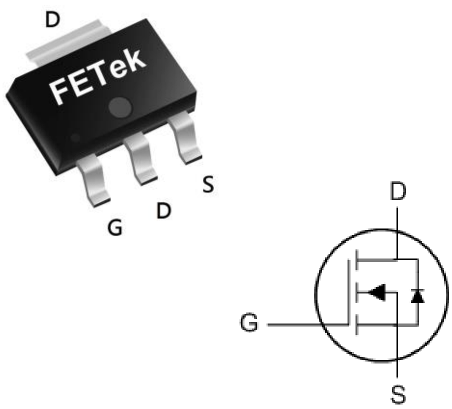
BVDSS	RDSON	ID
100V	310mΩ	2.2A

Description

The FKL0008 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The FKL0008 meet the RoHS and Green Product requirement with full function reliability approved.

SOT223 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	2.2	A
I_D@T_A=70˚C	Continuous Drain Current, V_{GS} @ 10V[1]	1.7	A
I_{DM}	Pulsed Drain Current[2]	5.5	A
P_D@T_A=25˚C	Total Power Dissipation[3]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJA}$	Thermal Resistance Junction-ambient [1]	---	85	˚C/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	---	36	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
△BV_{DSS}/△T_J	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.067	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=2A	---	260	310	mΩ
		V_{GS}=4.5V , I_D=1A	---	270	320	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.2	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	5	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=2A	---	2.4	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.8	5.6	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=50V , V_{GS}=10V , I_D=2A	---	9.3	12.7	nC
Q_{gs}	Gate-Source Charge		---	2	2.8	
Q_{gd}	Gate-Drain Charge		---	1.5	2.0	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3.3Ω I_D=2A	---	2	4.0	ns
T_r	Rise Time		---	21.6	39	
$T_{d(off)}$	Turn-Off Delay Time		---	11.2	22	
T_f	Fall Time		---	18.8	37.6	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	510	711	pF
C_{oss}	Output Capacitance		---	30	41	
C_{rss}	Reverse Transfer Capacitance		---	16	23	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	2.2	A
I_{SM}	Pulsed Source Current[2,4]		---	---	5.5	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=2A , dI/dt=100A/µs , T_J=25℃	---	17.5	---	nS
Q_{rr}	Reverse Recovery Charge		---	14	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150℃ junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

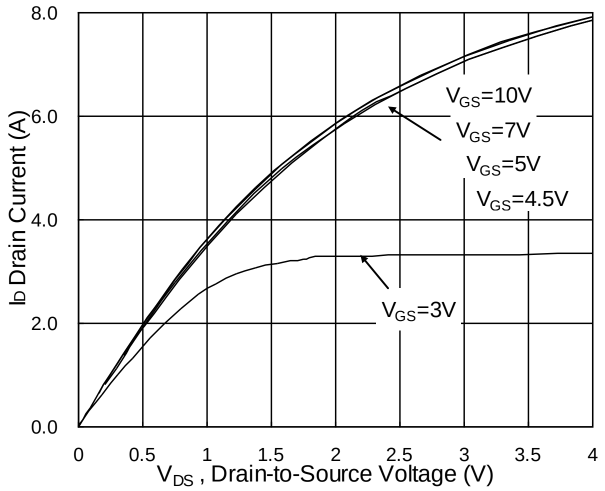


Fig.1 Typical Output Characteristics

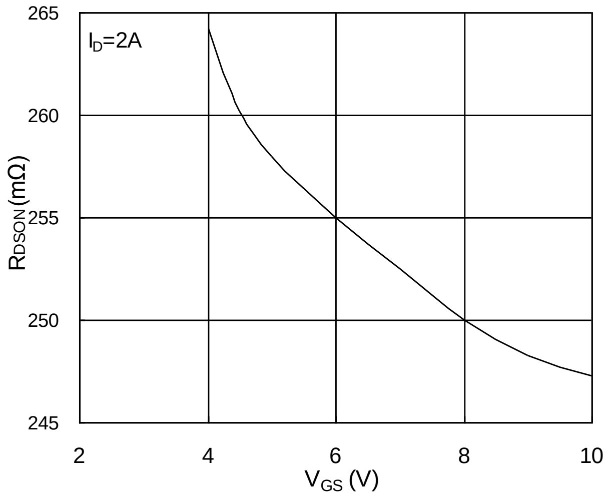


Fig.2 On-Resistance vs. Gate-Source

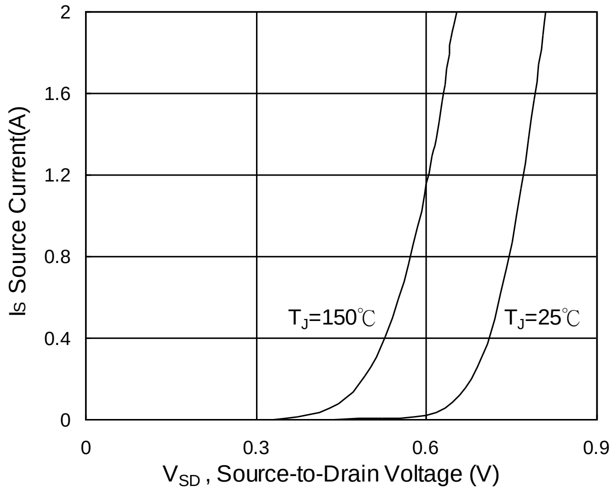


Fig.3 Forward Characteristics of Reverse

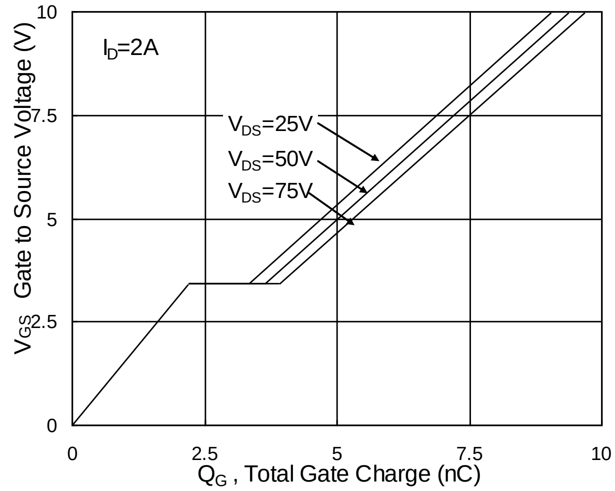


Fig.4 Gate-Charge Characteristics

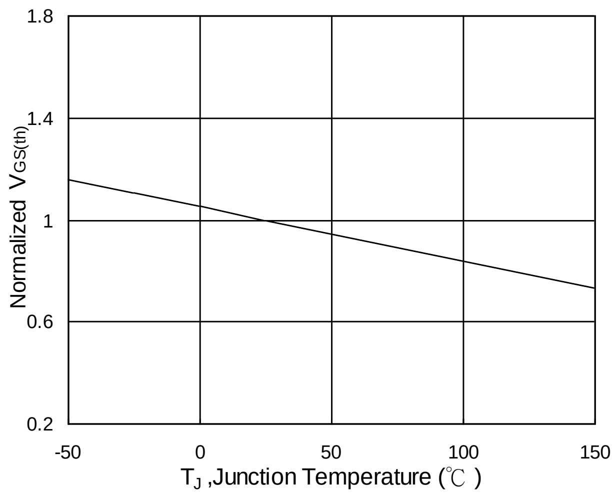


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

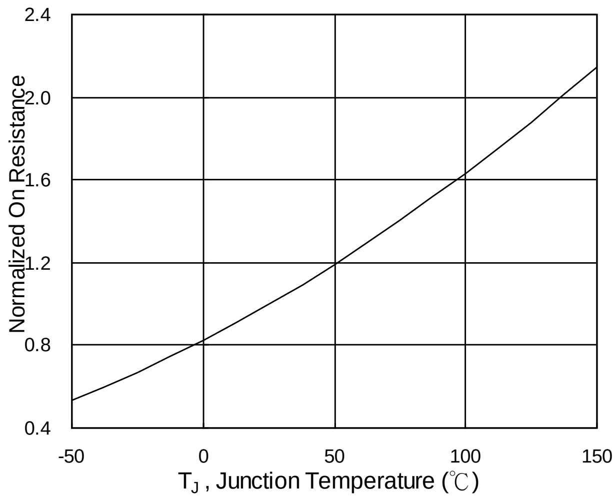


Fig.6 Normalized R_{DSON} vs. T_J

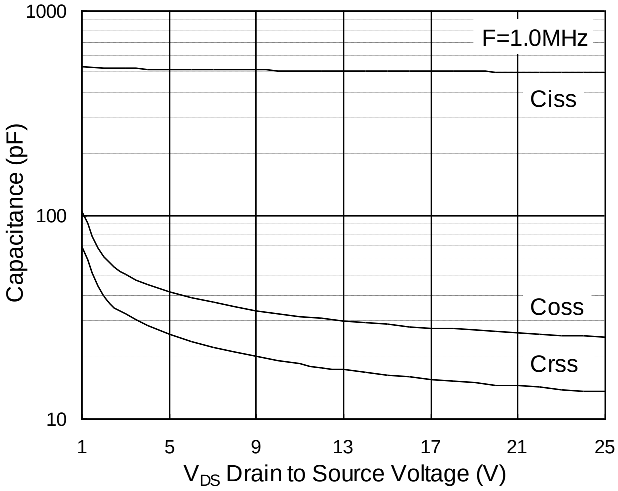


Fig.7 Capacitance

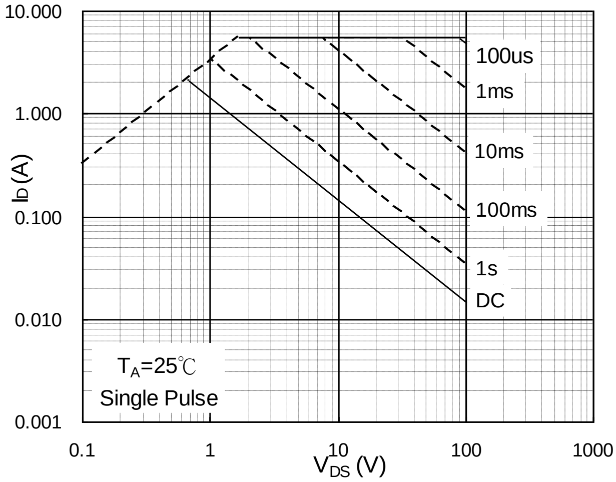


Fig.8 Safe Operating Area

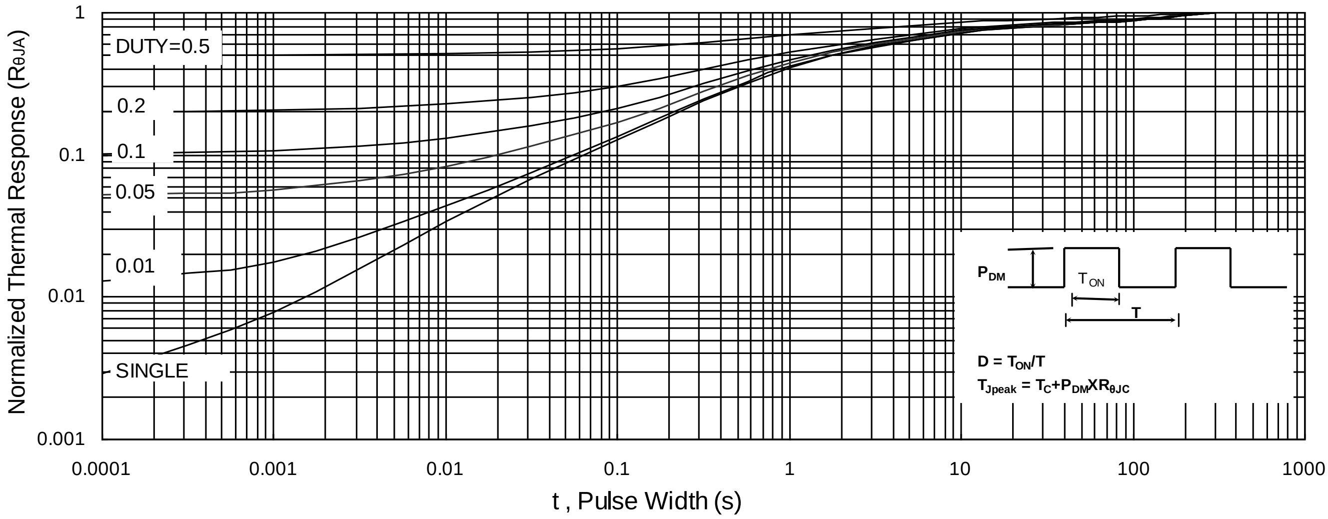


Fig.9 Normalized Maximum Transient Thermal Impedance

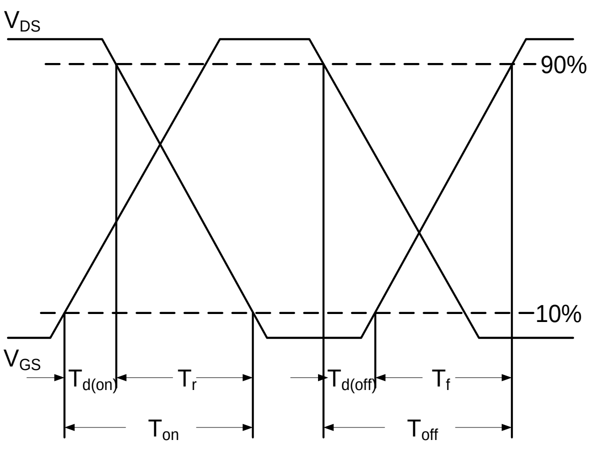


Fig.10 Switching Time Waveform

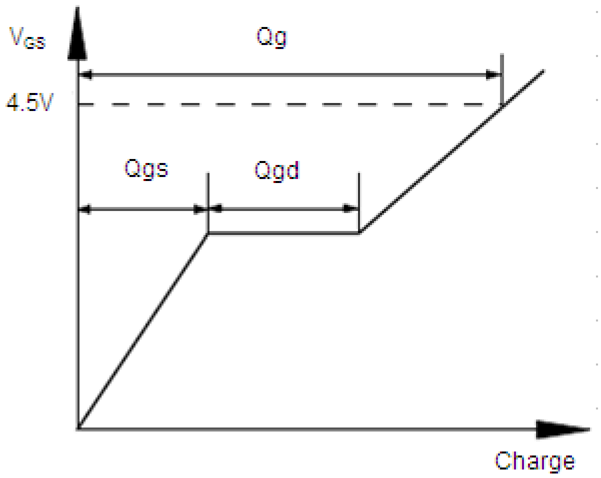


Fig.11 Gate Charge Waveform